imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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High Power Infrared Emitter (940nm) in SMR® Package Version 1.3

SFH 4542



Features:

- High Power Infrared LED
- SMR® (Surface Mount Radial) package
- Same package as photodiode SFH 2500
- Short switching times

Applications

- Sensor technology
- Discrete interrupters
- Discrete optocouplers

Notes

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

Ordering Information

Туре:	Radiant Intensity	Ordering Code
	l _e [mW/sr]	
	I _F = 100 mA, t _p = 20 ms	
SFH 4542	230 (≥ 100)	Q65110A8093
SFH 4542-BWCW	160 500	Q65111A7727

Note: Measured at a solid angle of $\Omega = 0.01 \text{ sr}$



Maximum Ratings (T_A = 25 °C)

Parameter	Symbol	Values	Unit
Operation and storage temperature range	T _{op} ; T _{stg}	-40 85	°C
Reverse voltage	V _R	5	V
Forward current	I _F	100	mA
Surge current $(t_p \le 100 \ \mu s, D = 0)$	I _{FSM}	1	A
Power consumption	P _{tot}	180	mW
ESD withstand voltage (acc. to ANSI/ ESDA/ JEDEC JS-001 - HBM)	V _{ESD}	2	kV
Thermal resistance junction - ambient 1) page 9	R _{thJA}	300	K/W

Characteristics (T_A = 25 °C)

Parameter		Symbol	Values	Unit
Peak wavelength (I _F = 100 mA, t _p = 20 ms)	(typ)	λ_{peak}	950	nm
Centroid wavelength $(I_F = 100 \text{ mA}, t_p = 20 \text{ ms})$	(typ)	$\lambda_{centroid}$	940	nm
Spectral bandwidth at 50% of I_{max} ($I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$)	(typ)	Δλ	42	nm
Halfangle	(typ)	φ	± 10	0
Dimensions of active chip area	(typ)	LxW	0.3 x 0.3	mm x mm
Rise and fall time of I_e (10% and 90% of $I_{e max}$) (I_F = 100 mA, R_L = 50 Ω)	(typ)	t _r , t _f	12	ns
Forward voltage (I _F = 100 mA, t _p = 20 ms)	(typ (max))	V _F	1.5 (≤ 1.8)	V
Forward voltage (I _F = 1 A, t _p = 100 μs)	(typ (max))	V _F	2.3 (≤ 3)	V
Reverse current (V _R = 5 V)		I _R	not designed for reverse operation	μA
Total radiant flux (I _F =100 mA, t _p =20 ms)	(typ)	Φ _e	65	mW
Temperature coefficient of I_e or Φ_e (I_F = 100 mA, t_p = 20 ms)	(typ)	TCI	-0.5	% / K
Temperature coefficient of V_F ($I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$)	(typ)	TC _V	-1.3	mV / K
Temperature coefficient of wavelength $(I_F = 100 \text{ mA}, t_p = 20 \text{ ms})$	(typ)	TC _λ	0.3	nm / K

$arouping (r_A = 20^{\circ} 0)$			
Group	Min Radiant Intensity Max Radiant Intensity		Typ Radiant Intensity
	l _F = 100 mA, t _p = 20 ms	l _F = 100 mA, t _p = 20 ms	I _F = 1 A, t _p = 25 μs
	I _{e, min} [mW / sr]	I _{e, max} [mW / sr]	I _{e, typ} [mW / sr]
SFH4542 - AW	100	200	1000
SFH4542 - BW	160	320	1700
SFH4542 - CW	250	500	2600

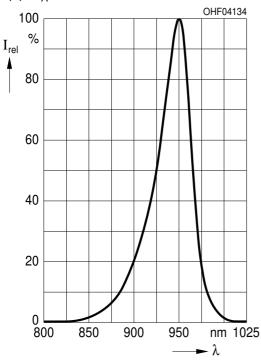
Grouping ($T_A = 25 \ ^\circ C$)

Note: measured at a solid angle of $\Omega = 0.01$ sr

Only one group in one packing unit (variation lower 2:1).

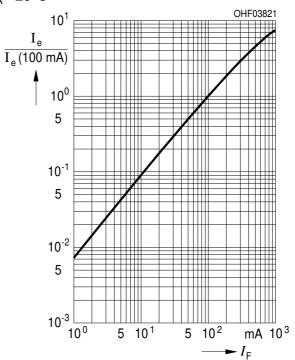


 $I_{rel} = f(\lambda), T_A = 25^{\circ}C$

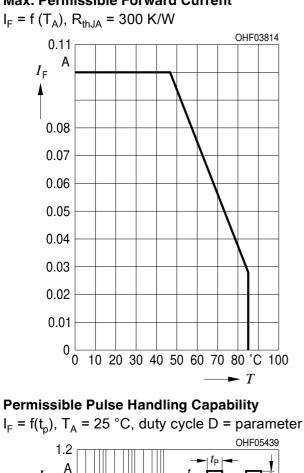


Radiant Intensity 2) page 9

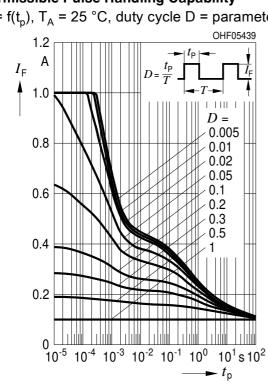
 I_e / I_e (100 mA) = f(I_F), single pulse, t_p = 25 µs, T_A = 25°C



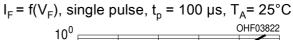


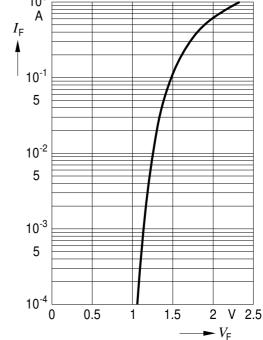


Max. Permissible Forward Current



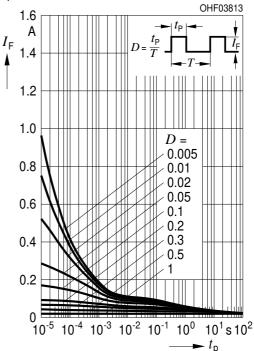
Forward Current ^{2) page 9}





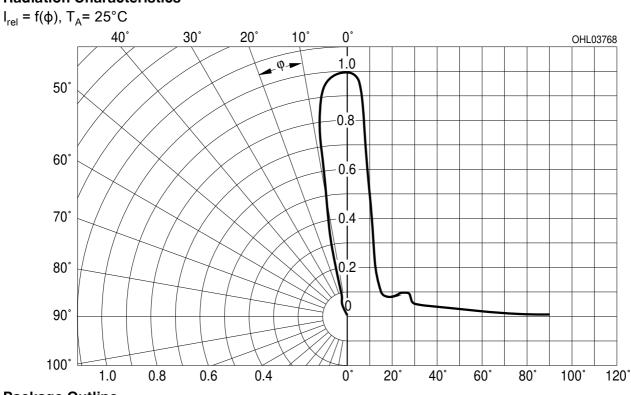
Permissible Pulse Handling Capability

 $I_F = f(t_p), T_A = 85 \ ^{\circ}C, duty cycle D = parameter$

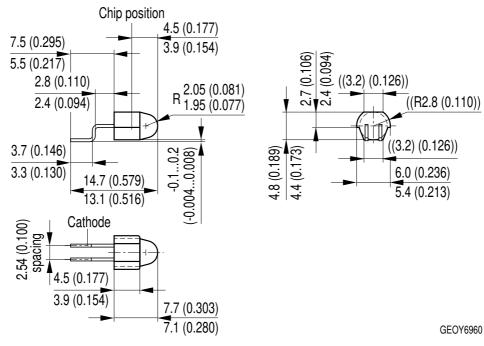




Radiation Characteristics ^{2) page 9}







Dimensions in mm (inch).

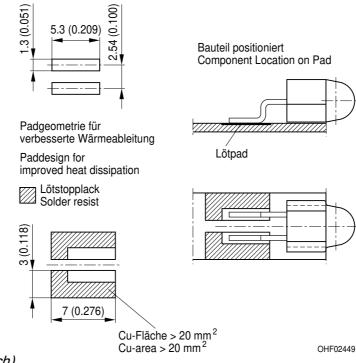
Approximate Weight: 0.2 g



Note

Packing information is available on the internet (online product catalog).

Recommended Solder Pad

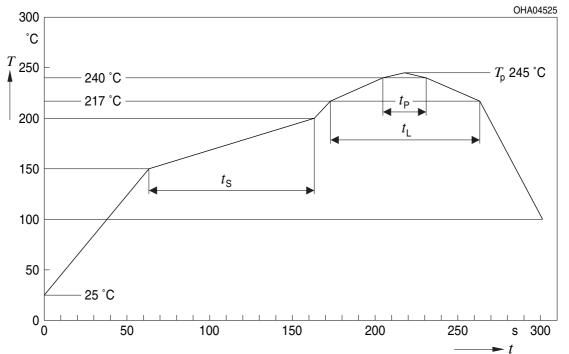


Dimensions in mm (inch).



Reflow Soldering Profile

Product complies to MSL Level 3 acc. to JEDEC J-STD-020D.01



			OHA046			
Profile Feature Profil-Charakteristik	Symbol	Pb-Free (SnAgCu) Assembly			Unit	
	Symbol	Minimum	Recommendation	Maximum	Einheit	
Ramp-up rate to preheat ^{*)} 25 °C to 150 °C			2	3	K/s	
Time t _S T _{Smin} to T _{Smax}	t _s	60	100	120	S	
Ramp-up rate to peak ^{*)} T _{Smax} to T _P			2	3	K/s	
Liquidus temperature	TL		217		°C	
Time above liquidus temperature	tL		80	100	s	
Peak temperature	T _P		245	260	°C	
Time within 5 °C of the specified peak temperature T_P - 5 K	t _P	10	20	30	S	
Ramp-down rate* T _P to 100 °C			3	6	K/s	
Time 25 °C to T _P				480	S	

All temperatures refer to the center of the package, measured on the top of the component

* slope calculation DT/Dt: Dt max. 5 s; fulfillment for the whole T-range



Disclaimer

Language english will prevail in case of any discrepancies or deviations between the two language wordings.

Attention please!

The information describes the type of component and shall not be considered as assured characteristics.

Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version in the Internet.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose! Critical components* may only be used in life-support devices** or systems with the express written approval of OSRAM OS.

*) A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or the effectiveness of that device or system.

**) Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health and the life of the user may be endangered.



Glossary

- ¹⁾ Thermal resistance: junction -ambient, mounted on PC-board (FR4), padsize 20 mm² each
- ²⁾ Typical Values: Due to the special conditions of the manufacturing processes of LED, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.

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EU RoHS and China RoHS compliant product

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